

The order-disorder character of the (3×3) to $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase transition of Sn on Ge(111)

L. Petaccia,¹ L. Floreano,^{1,*} A. Goldoni,² D. Cvetko,^{1,2,3} A. Morgante,^{1,4} L. Grill,¹ A. Verdini,¹ G. Comelli,^{1,4} G. Paolucci,² and S. Modesti^{1,4}

¹ *Laboratorio TASC, Istituto Nazionale per la Fisica della Materia, Basovizza SS14 Km 163.5, I-34012 Trieste, Italy*

² *Sincrotrone Trieste SCpA, Basovizza SS14 Km 163.5, I-34012 Trieste, Italy*

³ *Jožef Stefan Institute, Department of Physics, Ljubljana University, Ljubljana, Slovenia*

⁴ *Department of Physics, University of Trieste, Via Valerio 2, I-34100 Trieste, Italy*

The α -phase of Sn/Ge(111) has been investigated from 120 K up to 500 K, using synchrotron radiation core level photoemission. By means of photoelectron diffraction experiments, we verified that the rippled structure of the low temperature (3×3) -phase is preserved in the $(\sqrt{3} \times \sqrt{3})R30^\circ$ -phase at room temperature, thus confirming the order-disorder character of the phase transition. We also found that at least two components are present in the Sn 4d core level spectra up to 500 K, i.e about 300 K above the onset of the transition from the low temperature (3×3) -phase to the $(\sqrt{3} \times \sqrt{3})R30^\circ$ -phase, thus excluding the occurrence of any displacive transition.

PACS numbers: 61.14Qp, 68.35Bs, 79.60Dp

*Corresponding Author: Luca Floreano, Surface Division, Laboratorio TASC-INFN, Basovizza, SS14 Km 163.5 I-34012 Trieste, Italy. E-mail: floreano@sci.area.trieste.it

The system formed by one third of a monolayer (ML) of Sn adatoms atop the T_4 sites of the Ge(111) surface (α -phase) exhibits a transition from a low temperature (LT) (3×3) phase to a high temperature (HT) $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase. This transition is gradual, reversible and has a critical temperature $T_c \sim 220$ K. The phase transition was first attributed to the manifestation of a commensurate surface charge density wave state in the LT phase stabilized by many body effects, in particular by electron correlation.¹⁻⁴ Later on, an order-disorder model,⁵ invoking dynamic fluctuations as microscopic driving mechanism,⁶ has been proposed to explain the published data. The research then focused on the role of surface defects^{7,8} and the determination of the surface structure⁹⁻¹² in an attempt to discriminate between the two interpretations.

At present, the (3×3) structure has been determined with a good agreement between surface X-ray diffraction^{9,10} (SXRD) and photoelectron diffraction¹² (PED) measurements. At low temperature, the Sn adatoms occupy inequivalent T_4 sites, with one Sn adatom (out of three within the unit cell) protruding above the surface. This inequivalency is also confirmed by photoemission experiments, where at least two components (with intensity ratio close to 1:2) are required to fit the Sn 4d spectrum properly.^{5,11-14}

For the structure of the $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase at room temperature (RT), only SXRD measurements are available.^{9,10} They slightly favor a structure with equivalent Sn adatoms, thus suggesting that the transition is indeed due to a pseudo-Jahn-Teller effect,⁹ i.e. it would be a displacive phase transition. This result is hardly conciliating with a very recent He diffraction study of the (3×3) order parameter, which indicates the occurrence of a 3-state Potts order-disorder phase transition at $T_c \sim 220$ K.¹⁵ Moreover, the hypothesis of a displacive transition at 220 K is also not compatible with the core level photoemission experiments, where the inequivalency between the Sn atoms seems to remain also in the $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase, since the Sn 4d line-shape does not change significantly from ~ 100 -150 K up to room temperature.^{5,6,13,16} This discrepancy urges for PED structural measurements of the RT phase.

The hypothesis of a displacive transition, being recently suggested to be driven by a phonon softening,¹⁷ asks for experiments in a more extended temperature range. To our knowledge no data have been published at temperatures higher than 300 K, while it is well known that the displacive phase transitions are always accompanied by an intermediate disordered stage around the critical temperature,¹⁸⁻²⁰ manifesting the change in surface corrugation only at a temperature substantially higher than T_c . It is therefore of utmost importance to have a clear indication of the order-disorder character of the transition around T_c and to know if the two components observed in the Sn 4d core level spectra at LT and RT are also present far from T_c , up to the highest temperature

where this phase is stable (~ 550 K).²¹

By means of photoelectron diffraction (PED) measurements, we have already shown that in the (3×3) phase the observed splitting of the Sn 4d core levels in two components derives from adatoms with different bonding configuration.¹¹ A vertical ripple of 0.3 Å between the Sn adatoms has been estimated by simulations, with one adatom out of three that protrudes above the surface. In particular, the adatom at the higher height level is associated to the Sn 4d component with the larger binding energy.¹² The three nearest-neighbor Ge atoms follow the Sn adatom vertical distortion, i.e. their bond angle and length remain almost unchanged. This rippled structure is in good agreement with both the SXRD experiments⁹ and recent density- functional theory (DFT) calculations^{22,23} for the LT (3×3) -phase.

In this paper, we report on the evolution of the Sn 4d core levels and on their PED patterns at different temperatures. The measurements were performed at the ELETTRA Synchrotron facility in Trieste, in the ultra high vacuum end-stations of the ALOISA^{24,25} and SuperESCA²⁶ beamlines. The Sn 4d core levels photoemission spectra presented here were measured at the SuperESCA beamline with an overall energy resolution better than 120 meV. The PED experiments were performed at the ALOISA beamline.

Details about the sample preparation and PED experiment at ALOISA are given elsewhere.¹² At the SuperESCA beamline, the α -phase was prepared by dosing 1/3 ML of Sn on a clean Ge(111)-c(2 × 8) surface kept at RT. The optimum coverage and annealing treatment for the $(\sqrt{3} \times \sqrt{3})R30^\circ$ and (3×3) phases was checked by optimizing the intensity of the LEED (3×3) extra spots of the LT phase and the intensity of the Sn induced surface band at the Fermi level in the photoemission spectra. This feature is indeed very sensitive to the quality of the $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase.^{4,16} We have investigated also the (2×2) phase of Sn/Ge(111), obtained by dosing ~ 0.2 ML of Sn and annealing at 450 K. The temperature stability during measurements was better than ± 10 K.

In Fig. 1, we show the Sn 4d core level photoemission spectra taken at room temperature in normal emission geometry for photon energies between 120 and 300 eV. In these experimental conditions, the photon energy dependence of the photoemission spectra (after normalization to the photoemission cross-section) mainly reflects the vertical distance between the Sn adatom and the Ge atom directly underneath, thus enhancing the sensitivity to the vertical distortions of the adatom layer.¹¹ In fact, the Sn vertical ripple is the main structural parameter involved in the phase transition, since it is expected to disappear in the high temperature phase if a displacive transition takes place. A detailed description of the Sn 4d core level analysis in terms of two spin-orbit split doublets is given in Ref.¹², where high resolution spectra have been studied to determine the fitting parameters used for the successive analysis of the PED data taken in the LT phase. Also in the $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase at 300 K,

the Sn 4d core levels have a shape that cannot be fitted with a single spin-orbit split doublet.^{5,6,13,16} At least one additional doublet is needed to improve appreciably the quality of the fit (see the inset panel of Fig. 1).

The photon energy dependence of the intensity ratio I_B/I_A between the minority B and the majority A components of the Sn 4d_{5/2} core levels at 130 K and 300 K is shown in Fig. 2. This presentation of the PED data allows a direct evaluation of any change of the Sn vertical ripple, in particular, the disappearance of the ripple would yield a constant intensity ratio without any energy modulation. In addition, the comparison between the intensity ratio below and above the transition is not affected by the systematic errors of extracting the anisotropy χ -function. These errors can be large around 130 eV, because of the pronounced Cooper minimum. The error bars in Fig. 2 represent the maximum error in the intensity ratio, as obtained by the fitting procedure of ref.¹², and it mainly arises from the uncertainty on the energy shift between the A and B components and their linewidth. The intensity ratio I_B/I_A below and above the phase transition is very similar, confirming that, also in the $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase at RT, there are two inequivalent types of Sn adatoms with different bonding geometry (different vertical distances between Sn and the underneath Ge atom). Thus, the rippled structure is maintained up to RT. This result differs from that obtained by SXRD experiments^{10,9} (where the surface corrugation was claimed to change from the (3×3) to the $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase), and indicates that the phase transition at $T_c \sim 220$ K has an order-disorder character.

Since the two spectral components are unambiguously assigned to two adsorption sites with different Sn heights, we can detect any structural modification of the $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase by simply measuring the Sn 4d spectrum as a function of the temperature. In particular, an eventual merge of the two spectral components in a single one would be the fingerprint of a displacive transition. We have reported in Fig. 3 the lineshapes of the Sn 4d core level spectra of 1/3 ML of Sn/Ge(111) measured from 120 K to 500 K with a photon energy of 198 eV and an emission angle of 55° from the surface normal. These spectra have been fitted to Doniach Sunjic (DS) doublets convoluted with a Gaussian. The Gaussian takes into account both the instrumental broadening (120 meV) and the temperature dependent phonon broadening, that is much larger. The free parameters were the energy position of the doublets, their intensities, the Gaussian full width at half maximum (FWHM) [assumed to be the same for all the doublets], the asymmetry of the DS line, and the branching ratio. The spin-orbit splitting was set to 1.02 eV (according to Refs.^{13,28} and a polynomial function was used for the background caused by the low energy tail of the Ge 3d core levels at about 29 eV of binding energy.

Besides the A and B components, a third weak doublet was required to fit properly the (3×3) phase spectra

at 120 K. This component is attributed to the Sn atoms surrounding Ge substitutional impurities in the (3×3) overlayer, according to the measurements of Uhrberg et al.¹⁶. We observed that the third component intensity decreases by increasing the temperature up to disappearance at 420 K. This is possibly due to limits of the fitting procedure in detecting such a faint feature when the main components become increasingly broader.¹⁶ The energy shift between the A and B components does not change between 120 K and 500 K (see the upper panel of Fig. 4), while the corresponding gaussian width gradually broadens from ~ 0.3 eV up to ~ 0.5 eV. The Sn 4d core level lineshape at 500 K is more symmetric and can be fitted to a single DS doublet, thus yielding a Gaussian FWHM of ~ 0.6 eV, a value much larger than that of the components used to fit the low temperature spectra.

In order to discriminate between the model with a single component at 500 K and that with A and B components, we have followed the temperature dependence of the Gaussian FWHM of these components in the (3×3) , in the $(\sqrt{3} \times \sqrt{3})R30^\circ$ and in the (2×2) phases of Sn on Ge(111). The corresponding temperature dependences are reported in Fig. 4. The values obtained for the A and B components of the α -phase and for the (2×2) phase show a linear increase with the temperature, with a slope of $(0.5 \pm 0.02) \cdot 10^{-3}$ eV K⁻¹ and $(0.32 \pm 0.03) \cdot 10^{-3}$ eV K⁻¹, respectively. This result is consistent with the linear increase ($\sim 0.2 \cdot 10^{-3}$ eV K⁻¹) observed for the surface components of the 3d core levels of the clean Ge(111) surface in a wider temperature range.²⁷ The fit of the α -phase core levels with a single component yields a gaussian width which does not change with the temperature, while the quality of the fit declines as the temperature is lowered (being definitely insufficient already at 300 K). If the 500 K spectra contained a single component, there would be a jump of ~ 0.2 eV of the FWHM between 300 K and 500 K, with about a threefold increase in the temperature derivative of the core level width. This implies that the thermal broadening of the Sn 4d core levels would be strongly non linear, in contrast to the data of the Sn (2×2) phase, the clean Ge(111) surface and other semiconductors surfaces.^{28,29} As a consequence, the temperature dependence of the FWHMs reported in Fig. 4 strongly supports a deconvolution of the Sn 4d core level spectra with at least two DS doublets up to 500 K.

In conclusion, we have measured the temperature and energy dependence of the Sn 4d core levels of Sn/Ge(111). By means of energy dependent PED, we found that the vertical distortion, obtained for the two kinds of Sn adatoms in the LT (3×3) phase, is also present in the $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase at RT, i.e. the transition at ~ 220 K has an order-disorder character. In addition, we have shown that the two components of the photoemission spectra, reflecting the inequivalence of the Sn adsorption sites, are present up to 500 K. This result leads us to discard the occurrence of a displacive charac-

ter of the transition even at temperatures much higher than $T_c = 220$ K.

This work was partly supported by MURST cofin99 (Prot. 9902332155 and Prot. 9902112831), by Regione Friuli-Venezia Giulia 98 and by INFN PAIS-F99.

-
- ¹ J.M. Carpinelli, H.H. Weitering, E.W. Plummer, and R. Stumpf, *Nature* **381**, 398 (1996).
 - ² J.M. Carpinelli, H.H. Weitering, M. Bartkowiak, R. Stumpf, and E.W. Plummer, *Phys. Rev. Lett.* **79**, 2859 (1997).
 - ³ G. Santoro, S. Sorella, F. Becca, S. Scandolo, and E. Tosatti, *Surf. Sci.* **402-404**, 802 (1998); G. Santoro, S. Scandolo, E. Tosatti, *Phys. Rev. B* **59**, 1891 (1999).
 - ⁴ A. Goldoni and S. Modesti, *Phys. Rev. Lett.* **79**, 3266 (1997); **81**, 3553 (1998).
 - ⁵ R.I.G. Uhrberg and T. Balasubramanian, *Phys. Rev. Lett.* **81**, 2108 (1998).
 - ⁶ J. Avila, A. Mascaraque, E.G. Michel, M.C. Asensio, G. Le Lay, J. Ortega, R. Pérez, and F. Flores, *Phys. Rev. Lett.* **82**, 442 (1999).
 - ⁷ A.V. Melechko, J. Braun, H.H. Weitering, and E.W. Plummer, *Phys. Rev. Lett.* **83**, 999 (1999); *ibidem* *Phys. Rev. B* **61**, 2235 (2000).
 - ⁸ H.H. Weitering, J.M. Carpinelli, A.V. Melechko, J. Zhang, M. Bartkowiak, and E.W. Plummer, *Science* **285**, 2107 (1999).
 - ⁹ O. Bunk, J.H. Zeysing, G. Falkenberg, R.L. Johnson, M. Nielsen, M.M. Nielsen, and R. Feidenhans'l, *Phys. Rev. Lett.* **83**, 2226 (1999).
 - ¹⁰ J. Zhang, Ismail, P.J. Rous, A.P. Baddorf, and E.W. Plummer, *Phys. Rev. B* **60**, 2860 (1999).
 - ¹¹ L. Floreano, L. Petaccia, M. Benes, D. Cvetko, A. Goldoni, R. Gotter, L. Grill, A. Morgante, A. Verdini, and S. Modesti, *Surf. Rev. Lett.* **6**, 1091 (1999).
 - ¹² L. Petaccia, L. Floreano, M. Benes, D. Cvetko, L. Grill, A. Goldoni, A. Morgante, A. Verdini, and S. Modesti, *Phys. Rev. B* **63**, 115406 (2001).
 - ¹³ G. Le Lay, V. Yu. Aristov, O. Boström, J.M. Layet, M.C. Asensio, J. Avila, Y. Huttel, A. Cricenti, *App. Surf. Sci.* **123/124**, 440 (1998).
 - ¹⁴ J. Avila, Y. Huttel, A. Mascaraque, G. LeLay, E.G. Michel, and M.C. Asensio, *Surf. Sci.* **433-435**, 327 (1999).
 - ¹⁵ L. Floreano, D. Cvetko, G. Bavdek, M. Benes, and A. Morgante, *Phys. Rev. B* **64**, 075405 (2001).
 - ¹⁶ R.I.G. Uhrberg, H.M. Zhang, and T. Balasubramanian, *Phys. Rev. Lett.* **85**, 1036 (2000).
 - ¹⁷ R. Perez, J. Ortega, and F. Flores, *Phys. Rev. Lett.*, **86** 4891 (2001).
 - ¹⁸ for a review on displacive phase transitions see, e.g., A.D. Bruce and R.A. Cowley, *Adv. Phys.* **29**, 219 (1980).
 - ¹⁹ for an overview on surface CDW transitions see, e.g., E. Tosatti, in *Electronic Surface and Interface States on Metallic Systems*, edited by E. Bertel and M. Donath (World Scientific, Singapore, 1995).
 - ²⁰ H. J. Ernst *et al.*, *Phys. Rev. B* **46**, 16081 (1992).
 - ²¹ T. Ichikawa and S. Ino, *Surf. Sci.* **105**, 394 (1981).
 - ²² S. de Gironcoli, S. Scandolo, G. Ballabio, G. Santoro and E. Tosatti, *Surf. Sci.* **454-456**, 172 (2000).
 - ²³ J. Ortega, R. Perez, and F. Flores, *J. Phys. Condens. Matter* **12**, L21 (2000).
 - ²⁴ L. Floreano, G. Naletto, D. Cvetko, R. Gotter, M. Malvezzi, L. Marassi, A. Morgante, A. Santaniello, A. Verdini, F. Tommasini and G. Tondello, *Rev. Sci. Instrum.* **70**, 3855 (1999).
 - ²⁵ Details about the ALOISA end station can be found at the [web address: "http://www.tasc.infn.it/tasc/lds/aloesa/aloesa.html"](http://www.tasc.infn.it/tasc/lds/aloesa/aloesa.html).
 - ²⁶ A. Baraldi *et al.*, *J. Electron Spectrosc. Relat. Phenom.* **76**, 145 (1995).
 - ²⁷ A. Goldoni, A. Santoni, M. Sancrotti, V. R. Dhanak, and S. Modesti, *Surf. Sci.* **382**, 336 (1997).
 - ²⁸ M. Gothelid, T. M. Grehk, M. Hammar, U.O. Karlsson, and S.A. Flodstrom, *Surf. Sci.* **328**, 80 (1995).
 - ²⁹ J.J. Paggel, W. Theis, K. Horn, Ch. Jung, C. Hellwig, and H. Petersen, *Phys. Rev. B* **50**, 18686 (1994).

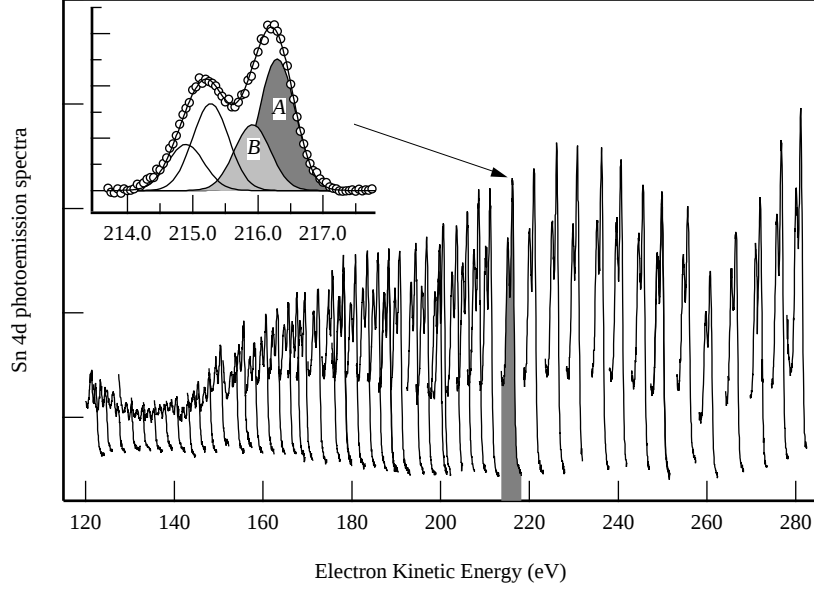


FIG. 1. Sn 4d photoemission spectra taken in normal emission from the $(\sqrt{3} \times \sqrt{3})R30^\circ$ phase at RT. Each spectrum has been taken at a different photon energy. The data have been normalized to the photon flux. The overall intensity slope clearly shows the Cooper's minimum for the Sn 4d core level at the lowest energies. The spectrum taken at $h\nu \sim 245$ eV is shown in the inset panel together with the fit to two doublets, after background correction.

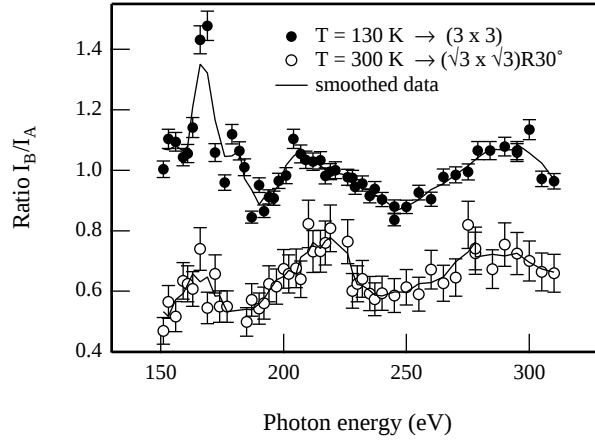


FIG. 2. Intensity ratio between the minority *B* and the majority *A* components of the Sn 4d_{5/2} core levels at 130 K (filled circles) and 300 K (open circles). The data at 130 K have been vertically shifted by 0.4 units for the sake of clarity. The smoothed data (full lines) are also shown as a guide to the eye.

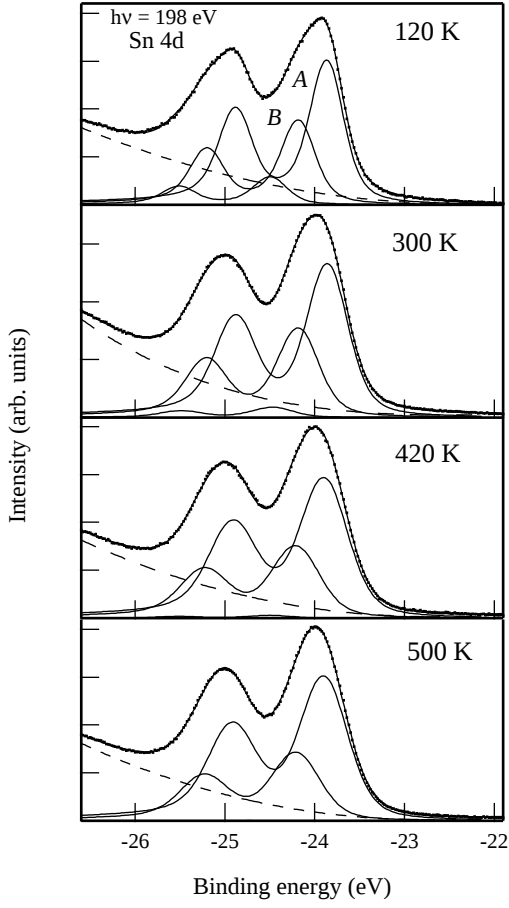


FIG. 3. Fit of the Sn 4d core levels with three DS spin-orbit split components in the (3×3) -phase at 120 K, and in the $(\sqrt{3} \times \sqrt{3})R30^\circ$ -phase at 300, 420 and 500 K. The fits yield a Lorentzian width of 0.2 eV with a branching ratio of 0.63 ± 0.01 and an intensity ratio of 0.52-0.6 between the *B* and *A* components.

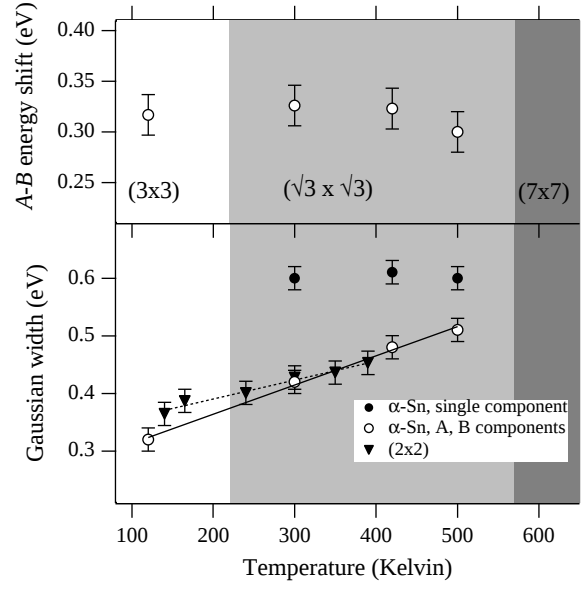


FIG. 4. Upper panel: temperature dependence of the energy shift between the *A* and *B* components as obtained by the fit to the Sn 4d spectra in Fig. 3. Lower panel: temperature dependence of the Gaussian FWHM as obtained from Fig. 3 (open circles). The filled circles show the Gaussian FWHM obtained by fitting the spectra of the α -phase to a single spin-orbit split component (DS type). The Gaussian FWHM of the Sn 4d spectra, taken in the (2×2) phase at 0.2 ML, is also reported (filled triangles). Full and dotted lines are linear fits to the temperature behaviour of the FWHMs.